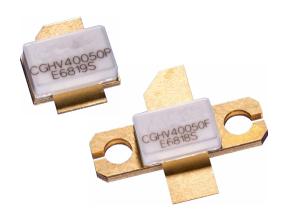


# CGHV40050

50 W, DC - 4.0 GHz, 50 V, GaN HEMT

#### **Description**

The CGHV40050 is an unmatched, gallium nitride (GaN) high electron mobility transistor (HEMT). The CGHV40050, operating from a 50 volt rail, offers a general purpose, broadband solution to a variety of RF and microwave applications up to 4 GHz. The reference HPA design in the datasheet operates from 800 MHz to 2 GHz operation instantaneously. It is a demonstration amplifier to showcase the CGHV40050's high efficiency, high gain and wide bandwidth capabilities. The device can be used for a range of applications from narrow band UHF, L and S Band as well as multi-octave bandwidth amplifiers up to 4 GHz. The transistor is available in a 2-lead flange and pill package.



Package Types: 440193 & 440206 PNs: CGHV40050F & CGHV40050P

#### Typical Performance Over 800 MHz - 2.0 GHz ( $T_c = 25^{\circ}$ C), 50 V

Parameter	800 MHz	1.2 GHz	1.4 GHz	1.8 GHz	2.0 GHz	Units
Small Signal Gain	17.6	16.9	17.7	17.5	14.8	dB
Saturated Output Power	65	70	63	77	60	W
Drain Efficiency @ P <sub>SAT</sub>	63	63	60	53	52	%
Input Return Loss	5	5.5	4.2	8	5	dB

Note: Measured CW in the CGHV40050F-AMP application circuit.

#### **Features**

- Up to 4 GHz Operation
- 77 W Typical Output Power
- 17.5 dB Small Signal Gain at 1.8 GHz
- Application Circuit for 0.8 2.0 GHz
- 53% Efficiency at P<sub>SAT</sub>
- 50 V Operation





Large Signal Models Available for ADS and MWO



#### Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V <sub>DSS</sub>	150	V	25°C
Gate-to-Source Voltage	V <sub>GS</sub>	-10, +2	V	25°C
Storage Temperature	T <sub>STG</sub>	-65, +150	°C	
Operating Junction Temperature	TJ	225	٦	
Maximum Forward Gate Current	I <sub>GMAX</sub>	10.4	mA	artic
Maximum Drain Current <sup>1</sup>	I <sub>DMAX</sub>	6.3	А	- 25°C
Soldering Temperature <sup>2</sup>	Ts	245	°C	
Screw Torque	τ	40	in-oz	
Thermal Resistance, Junction to Case <sup>3</sup>		3.04	06/14/	or0c
Thermal Resistance, Junction to Case⁴	R <sub>θJC</sub>	3.11	°C/W	85°C
Case Operating Temperature⁵	T <sub>c</sub>	-40, +80	°C	30 Seconds

#### Notoc

#### **Electrical Characteristics (T<sub>c</sub> = 25°C)**

Characteristics	Symbol	Min.	Тур.	Max.	Units	Conditions
DC Characteristics <sup>1</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10.4 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	_	V <sub>DC</sub>	$V_{DS} = 50 \text{ V}, I_{D} = 0.3 \text{ A}$
Saturated Drain Current <sup>2</sup>	I <sub>DS</sub>	6.8	9.7	_	Α	$V_{DS} = 6.0 \text{ V}, V_{GS} = 2.0 \text{ V}$
Drain-Source Breakdown Voltage	V <sub>BR</sub>	100	_	_	V <sub>DC</sub>	$V_{GS} = -8 \text{ V, } I_D = 10.4 \text{ mA}$
RF Characteristics <sup>3</sup> ( $T_c = 25^{\circ}C$ , $F_0 = 1$	L.8 GHz unl	ess othe	rwise no	ted)		
Small Signal Gain	Gss	17.5	19	_	dB	$V_{DD} = 50 \text{ V}, I_{DQ} = 0.3 \text{ A}$
Power Gain	G₽	ı	15.5	_	иь	$V_{DD} = 50 \text{ V}, I_{DQ} = 0.3 \text{ A}, P_{OUT} = P_{SAT}$
Output Power at Saturation <sup>4</sup>	P <sub>SAT</sub>	70	77	_	W	$V_{DD} = 50 \text{ V}, I_{DQ} = 0.3 \text{ A}$
Drain Efficiency	η	48	53	_	%	$V_{DD} = 50 \text{ V}, I_{DQ} = 0.3 \text{ A}, P_{OUT} = P_{SAT}$
Output Mismatch Stress	VSWR	ı	_	10:1	Ψ	No damage at all phase angles, $V_{DD} = 50 \text{ V}$ , $I_{DQ} = 0.3 \text{ A}$ , $P_{OUT} = 50 \text{ W}$ CW
Dynamic Characteristics						
Input Capacitance	C <sub>GS</sub>	_	16	_		
Output Capacitance	C <sub>DS</sub>		5	_	pF	$V_{DS} = 50 \text{ V}, V_{GS} = -8 \text{ V}, f = 1 \text{ MHz}$
Feedback Capacitance	$C_{\sf GD}$	_	0.3	_		

#### Notes

<sup>&</sup>lt;sup>1</sup> Current limit for long term, reliable operation

<sup>&</sup>lt;sup>2</sup> Refer to the Application Note on soldering

 $<sup>^{3}</sup>$  Measured for the CGHV40050P at  $P_{\text{DISS}}$  = 41.6 W

 $<sup>^{\</sup>rm 4}$  Measured for the CGHV40050F at P  $_{\rm DISS}$  = 41.6 W

 $<sup>^{\</sup>scriptscriptstyle 5}$  See also, Power Derating Curve on Page 7

 $<sup>^{\</sup>scriptscriptstyle 1}\,\text{Measured}$  on wafer prior to packaging.

<sup>&</sup>lt;sup>2</sup> Scaled from PCM data

<sup>&</sup>lt;sup>3</sup> Measured in CGHV40050-AMP

 $<sup>^4</sup>$  P<sub>SAT</sub> is defined as I<sub>G</sub>= 1 mA

<sup>&</sup>lt;sup>5</sup> Includes package



### **CGHV40050 Typical Performance**

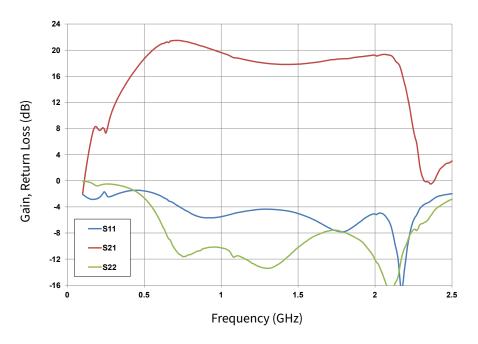
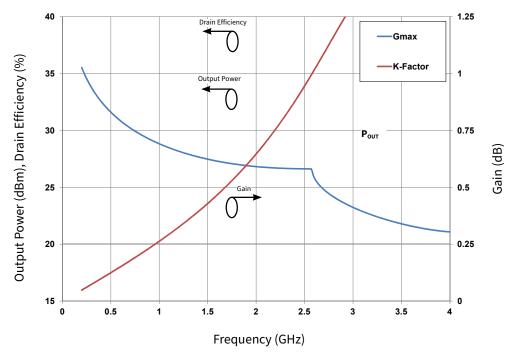


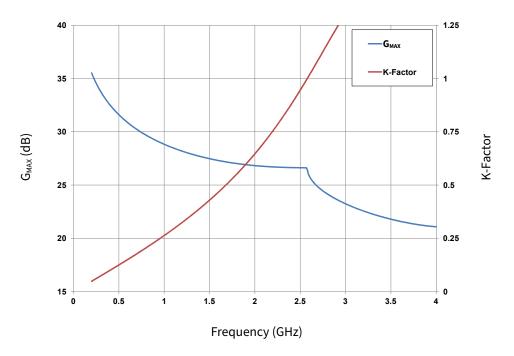
Figure 1. Small Signal Gain and Return Losses vs Frequency of the CGHV40050 in the application circuit CGHV40050-AMP  $V_{DD}=50~V,~I_{DQ}=300~mA,~T_{CASE}=25^{\circ}C$ 



**Figure 2.** Gain, Output Power and Drain Efficiency vs Frequency of the CGHV40050 measured in Broadband Amplifier Circuit CGHV40050-AMP  $V_{DD}=50~V,~I_{DQ}=300~mA,~T_{CASE}=25^{\circ}C$ 

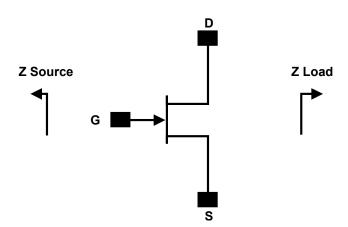


#### **CGHV40050 Typical Performance**



**Figure 3.**  $G_{MAX}$  and K-Factor vs Frequency  $V_{DD} = 50V$ ,  $I_{DQ} = 300$  mA,  $T_{CASE} = 25$ °C

#### **Source and Load Impedances**



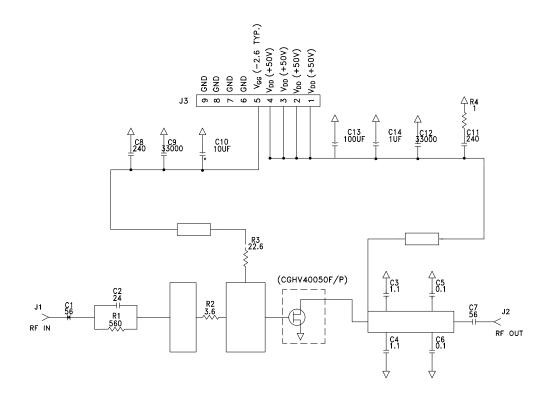
Frequency (MHz)	Z Source	Z Load
500	5.69+j7.82	21.47+j10.28
1000	3.21+j3.48	11.72+j10.50
2000	3.2-j1.74	3.84+j7.07
3000	3.23-j5.23	5.58+j3.02
4000	2.75-j10.6	4.65-j0.74

Note:  $V_{DD}$  = 50V,  $I_{DQ}$  = 300 mA in the 440193 package

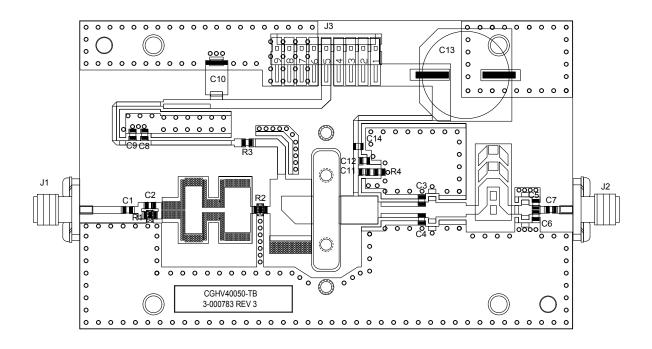
https://www.macom.com/support



## **CGHV40050-AMP Application Circuit Schematic**



#### **CGHV40050-AMP Application Circuit**

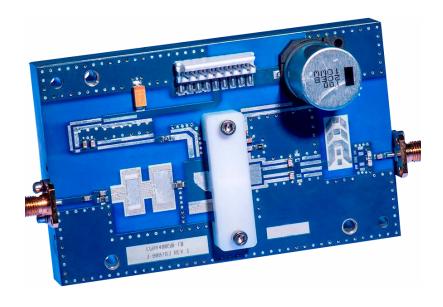




### **CGHV40050-AMP Application Circuit Bill of Materials**

Designator	Description	Qty
R1	RES, 560 Ohms, 0805, HIGH POWER SMT	1
R2	RES, 3.6 Ohms, 1005, HIGH POWER SMT	1
R3	RES, SMT, 0805, 22 OHM	1
R4	RES, SMT, 0805, 1 OHM	1
C1, C7	CAP, 56pF +/- 5%, 250V, 0805, ATC 600F	3
C2	CAP, 24pF +/- 5%, 250V, 0805, ATC 600F	1
C3, C4	CAP, 1.1pF, +/-0.1pF, 250V, 0805, ATC600F	2
C5, C6	CAP, 0.1pF +/- 0.05pF, 0805, ATC 600F	2
C8, C11	CAP, 240pF, +/-5%, 0805, ATC600F	2
C9, C12	CAP, 33000pF, 0805, 100V, X7R	2
C10	CAP, 10μF, 16V, TANTALUM	1
C13	CAP, 100μF, 80V, ELECTROLYTIC, CAN	1
C14	CAP, 1μF, 0805, 100V, X7S	1
J1,J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	2
J3	HEADER RT>PLZ .1CEN LK 9POS	1
-	BASEPLATE, CGH35120	1
-	PCB, RO4350B, 2.5"x4"x0.020", CGHV40050F	1

#### **CGHV40050-AMP Demonstration Amplifier Circuit**





### **CGHV40050 Power Dissipation De-rating Curve**

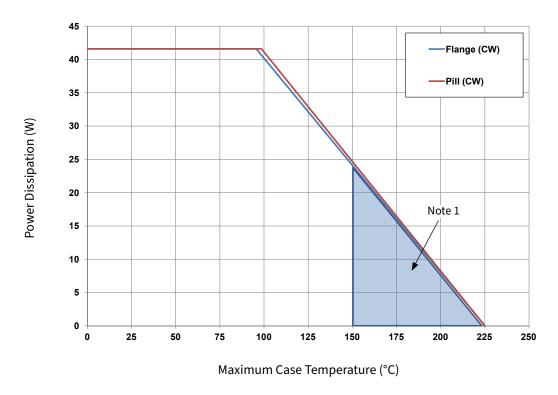


Figure 4. Transient Power Dissipation De-Rating Curve

Note:

#### **Electrostatic Discharge (ESD) Classifications**

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	НВМ	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	TBD	ANSI/ESDA/JEDEC JS-002 Table 3	JEDEC JESD22 C101-C

 $<sup>^{\</sup>rm 1}{\rm Area}$  exceeds Maximum Case Operating Temperature (See Page 2).



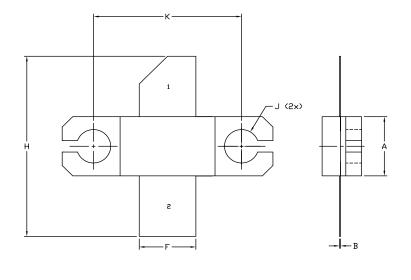
Typical S-Parameters (Small Signal,  $V_{DS} = 50 \text{ V}$ ,  $I_{DQ} = 300 \text{ mA}$ , magnitude / angle)

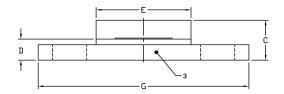
Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.92	-161.97	13.79	79.27	0.01	-5.56	0.44	-142.42
600 MHz	0.92	-165.42	11.38	74.02	0.01	-9.73	0.46	-143.34
700 MHz	0.92	-168.02	9.62	69.31	0.01	-13.32	0.49	-144.16
800 MHz	0.93	-170.08	8.29	64.99	0.01	-16.49	0.52	-145.04
900 MHz	0.93	-171.8	7.24	60.98	0.009	-19.32	0.55	-146.01
1.0 GHz	0.93	-173.27	6.4	57.23	0.009	-21.83	0.58	-147.07
1.1 GHz	0.93	-174.58	5.7	53.71	0.009	-24.07	0.61	-148.21
1.2 GHz	0.94	-175.77	5.13	50.38	0.008	-26.05	0.63	-149.4
1.3 GHz	0.94	-176.86	4.64	47.24	0.008	-27.77	0.65	-150.62
1.4 GHz	0.94	-177.89	4.23	44.25	0.007	-29.25	0.67	-151.85
1.5 GHz	0.94	-178.87	3.87	41.42	0.007	-30.48	0.69	-153.09
1.6 GHz	0.94	-179.81	3.56	38.72	0.007	-31.46	0.71	-154.33
1.7 GHz	0.95	179.28	3.3	36.14	0.006	-32.19	0.73	-155.54
1.8 GHz	0.95	178.4	3.06	33.68	0.006	-32.66	0.74	-156.74
1.9 GHz	0.95	177.53	2.85	31.32	0.006	-32.85	0.76	-157.91
2.0 GHz	0.95	176.67	2.67	29.06	0.005	-32.75	0.77	-159.06
2.1 GHz	0.95	175.82	2.51	26.88	0.005	-32.33	0.78	-160.18
2.2 GHz	0.95	174.97	2.37	24.78	0.005	-31.57	0.79	-161.28
2.3 GHz	0.95	174.13	2.24	22.75	0.005	-30.43	0.8	-162.34
2.4 GHz	0.96	173.28	2.12	20.78	0.004	-28.87	0.81	-163.39
2.5 GHz	0.96	172.43	2.02	18.87	0.004	-26.86	0.82	-164.4
2.6 GHz	0.96	171.57	1.93	17.02	0.004	-24.35	0.82	-165.4
2.7 GHz	0.96	170.7	1.85	15.2	0.004	-21.31	0.83	-166.37
2.8 GHz	0.96	169.82	1.77	13.43	0.003	-17.72	0.84	-167.32
2.9 GHz	0.96	168.92	1.71	11.69	0.003	-13.6	0.84	-168.25
3.0 GHz	0.96	168.01	1.65	9.98	0.003	-8.98	0.85	-169.17
3.2 GHz	0.96	166.12	1.55	6.62	0.003	1.31	0.86	-170.95
3.4 GHz	0.96	164.13	1.47	3.33	0.003	11.88	0.86	-172.69
3.6 GHz	0.96	162	1.41	0.06	0.004	21.35	0.87	-174.4
3.8 GHz	0.95	159.72	1.36	-3.22	0.004	28.89	0.87	-176.09
4.0 GHz	0.95	157.25	1.33	-6.55	0.005	34.35	0.88	-177.76

To download the s-parameters in s2p format, go to the CGHV40050 Product Page.



#### Product Dimensions CGHV40050F (Package Type — 440193)





#### NOTES

1. DIMENSIONING AND TOLERANICING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020' BEYOND EDGE OF LID.

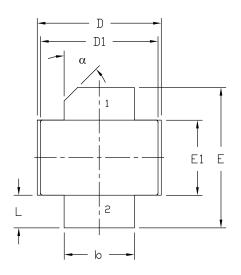
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008' IN ANY DIRECTION.

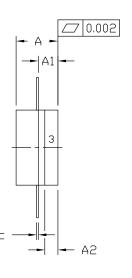
5. ALL PLATED SURFACES ARE NI/AU

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.225	0.235	5.72	5.97	
В	0.004	0.006	0.10	0.15	
С	0.145	0.165	3.68	4.19	
D	0.077	0.087	1.96	2.21	
Ε	0.355	0.365	9.02	9.27	
F	0.210	0.220	5.33	5.59	
G	0.795	0.805	20.19	20.45	
Н	0.670	0.730	17.02	18.54	
J	ø.	130	3.30		
k	0.5	62	14.	28	

PIN 1. GATE PIN 2. DRAIN PIN 3. SOURCE

## **Product Dimensions CGHV40050P (Package Type — 440206)**





#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M  $-\,$  1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
- 4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008' IN ANY DIRECTION.

	INCHES		MILLIM	NOTES	
DIM	MIN	MAX	MIN	MAX	
Α	0.125	0.145	3.18	3.68	
A1	0.057	0.067	1.45	1.70	
A2	0.035	0.045	0.89	1.14	
b	0.210	0.220	5.33	5.59	2x
C	0.004	0.006	0.10	0.15	2x
D	0.375	0.385	9.53	9.78	
D1	0.355	0.365	9.02	9.27	
E	0.400	0.460	10.16	11.68	
E1	0.225	0.235	5.72	5.97	
ш	0.085	0.115	2.16	2.92	2×
α	45*	REF	45°	45° REF	

PIN 1. GATE

- 2. DRAIN
- 3. SOURCE



# **Product Ordering Information**

Order Number	Description	Unit of Measure	Image
CGHV40050F	GaN HEMT	Each	CGHVA0050F
CGHV40050P	GaN HEMT	Each	CGHV40050P
CGHV40050F-AMP	Test board with GaN HEMT installed	Each	



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